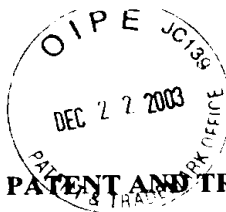


Docket No. 210136US99



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

IN RE APPLICATION OF: Ravindranath DROOPAD, et al.

SERIAL NO: 09/901,109

GAU: 2815

FILED: July 10, 2001

EXAMINER: BAUMEISTER

FOR: STRUCTURE AND METHOD FOR FABRICATING SEMICONDUCTOR STRUCTURES AND DEVICES
UTILIZING THE FORMATION OF A COMPLIANT SUBSTRATE COMPRISING AN OXYGEN-DOPED
COMPOUND SEMICONDUCTOR LAYER

INFORMATION DISCLOSURE STATEMENT UNDER 37 CFR 1.97

COMMISSIONER FOR PATENTS
ALEXANDRIA, VIRGINIA 22313

SIR:

Applicant(s) wish to disclose the following information.

REFERENCES

- ☒ The applicant(s) wish to make of record the references listed on the attached form PTO-1449. Copies of the listed references were submitted in application Serial No. 09/908,888 according to the attached copy of a Granted Petition. This application contains related subject matter.
- ☒ A check or credit card payment form is attached in the amount required under 37 CFR §1.17(p).

RELATED CASES

- ☐ Attached is a list of applicant's pending application(s) or issued patent(s) which may be related to the present application. A copy of the patent(s), together with a copy of the claims and drawings of the pending application(s) is attached along with PTO 1449.
- ☐ A check or credit card payment form is attached in the amount required under 37 CFR §1.17(p).

CERTIFICATION

- ☐ Each item of information contained in this information disclosure statement was first cited in a communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of this statement.
- ☐ No item of information contained in this information disclosure statement was cited in a communication from a foreign patent office in a counterpart foreign application or, to the knowledge of the undersigned, having made reasonable inquiry, was known to any individual designated in 37 CFR §1.56(c) more than three months prior to the filing of this statement.

DEPOSIT ACCOUNT

- ☒ Please charge any additional fees for the papers being filed herewith and for which no check or credit card payment is enclosed herewith, or credit any overpayment to deposit account number 15-0030. A duplicate copy of this sheet is enclosed.

12/30/2003 ARD0F01 00000089 09901109

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180.00 DP

Respectfully submitted,

OBLON, SPIVAK, McCLELLAND,
MAIER & NEUSTADT, P.C.

Richard L. Treanor

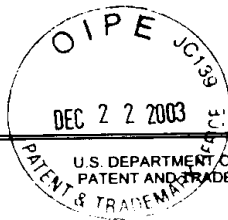
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LIST OF REFERENCES CITED BY APPLICANT

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GROUP

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U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
	XN	6,233,435 B1	05/15/01	WONG			
	XO	4,723,321	02/02/88	SALEH			
	XP	6,181,920 B1	01/30/01	DENT ET AL			
	XQ	6,415,140 B1	07/02/02	BENJAMIN ET AL			
	XR	5,760,740	06/02/98	BLODGETT			
	XS	5,238,877	08/24/93	RUSSELL			
	XT	4,876,218	10/24/89	PESSA ET AL			
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	XV	4,378,259	03/29/83	HASEGAWA ET AL			
	XW	6,278,541 B1	08/21/01	BAKER			
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Examiner

Date Considered

*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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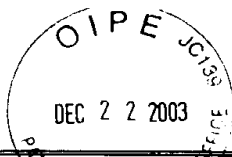
U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
	YQ	6,501,121 B1	12/31/02	YU ET AL			
	YR	5,919,515	07/06/99	YANO ET AL			
	YS	5,238,877	08/24/93	RUSSELL			
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	YW	5,365,477	11/15/94	COOPER, JR ET AL			
	YX	5,548,141	08/20/96	MORRIS ET AL			
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	ZB	5,313,058	05/17/94	FRIEDERICH ET AL			
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Examiner

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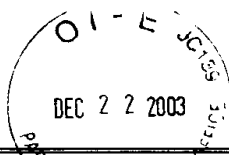
July 10, 2001

GROUP

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					YES	NO
	CCA	5-238894	09/17/93	JAPAN W/ENGLISH ABSTRACT		
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	CCC	2001-196892	07/19/01	JAPAN W/ENGLISH ABSTRACT		
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	CCF	1 043 427	10/11/00	EUROPE		
	CCG	1 069 605	01/17/01	EUROPE		
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	CCV					
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	CCX					
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LIST OF REFERENCES CITED BY APPLICANT				APPLICANT Ravindranath DROOPAD, et al.	
				FILING DATE July 10, 2001	GROUP 2815
OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)					
	LLAA	Peter Weiss; "Speed demon gets hooked on silicon"; Science News Online; Sept. 15, 2001; pp. 1-3			
	LLAB	"Motorola Develops New Super-Fast Chip"; USA Today; Sept. 4, 2001			
	LLAC	Lori Valigra; "Motorola Lays GaAs on Si Wafer"; AsiaBizTech; Nov. 2001pp. 1-3			
	LLAD	"Holy Grail! Motorola Claims High-Yield GaAs Breakthrough"; Micromagazine.com (no date available); pp. 1-3			
	LLAE	Jong-Gul YOON; "Growth of Ferroelectric LiNbO ₃ Thin Film on MgO-Buffered Si by the Sol-Gel Method"; Journal of the Korean Physical Society (Proc. Suppl.); Vol. 29, Nov. 1996; pp. S648-S651			
	LLAF	V. Bormand et al.; "Deposition of LiTaO ₃ thin films by pyrosol process"; Thin Solid Films 304 (1997); pp.239-244			
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	LLAH	A.K. Sharma et al.; "Integration of Pb(Zr _{0.52} Ti _{0.48})O ₃ epilayers with Si by domain epitaxy"; Applied Physics Letters, Vol. 76, No. 11; March 13, 2000; pp. 1458-1460			
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